

## PRELIMINARY

Notice: This is not a final specification  
Some parametric are subject to change.

# INC5004AC1

FOR HIGH CURRENT DRIVE APPLICATION  
SILICON NPN EPITAXIAL TYPE

## DESCRIPTION

INC5004AC1 is a silicon NPN epitaxial type transistor.  
It is designed with high collector current and small  $V_{CE(sat)}$ .

## FEATURE

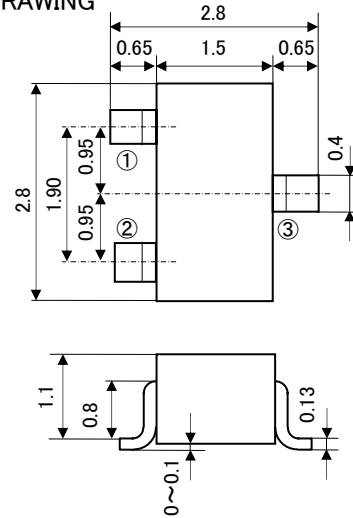
- Super mini package for easy mounting
- High collector current( $I_C=2A$ )
- Low collector saturation voltage  
( $V_{CE(sat)} < 0.15V_{max}$ ;  $I_C=1.5A$ ,  $I_B=30mA$ )

## APPLICATION

Switching, Small type motor drive

## OUTLINE DRAWING

UNIT: mm



Terminal Connector

JEITA:SC-59

①: Base

JEDEC: Similar to TO-236

②: Emitter

③: Collector

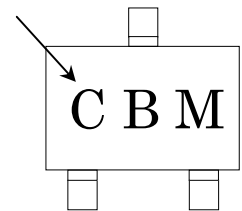
## MAXIMUM RATING ( $T_a=25^\circ C$ )

SYMBOL	PARAMETER	RATING	UNIT
$V_{CEO}$	Collector to Emitter voltage	20	V
$V_{CBO}$	Collector to Base voltage	50	V
$V_{EBO}$	Emitter to Base voltage	9	V
$I_C$	Collector current	5	A
$P_C$	Collector dissipation( $T_a=25^\circ C$ )	200	mW
		900(*)	
$T_j$	Junction temperature	+150	$^\circ C$
$T_{stg}$	Storage temperature	-55 ~ +150	$^\circ C$

\*Mounted on ceramic board(46mm × 19mm × 1mm)

## MARKING

Type Name



## ELECTRICAL CHARACTERISTICS ( $T_a=25^\circ C$ )

SYMBOL	PARAMETER	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
$V_{(BR)CEO}$	C to E break down voltage	$I_C=1mA$ , $I_B=0mA$	20	—	—	V
$V_{(BR)CBO}$	C to B break down voltage	$I_C=10\mu A$ , $I_E=0mA$	50	—	—	V
$V_{(BR)EBO}$	E to B break down voltage	$I_E=10\mu A$ , $I_C=0mA$	9	—	—	V
$I_{CBO}$	Collector cut off current	$V_{CB}=40V$ , $I_E=0mA$	—	—	0.1	$\mu A$
$I_{EBO}$	Emitter cut off current	$V_{EB}=7V$ , $I_C=0mA$	—	—	0.1	$\mu A$
$h_{FE1}$	DC forward current gain1	$V_{CE}=2V$ , $I_C=500mA$	230	—	600	—
$h_{FE2}$	DC forward current gain2	$V_{CE}=2V$ , $I_C=2A$	150	—	—	—
$V_{CE(sat)}$	C to E saturation voltage	$I_C=1.5A$ , $I_B=30mA$	—	0.12	0.15	V
$f_T$	Gain bandwidth product	$V_{CE}=6V$ , $I_E=-50mA$ , $f=100MHz$	—	150	—	MHz
$C_{ob}$	Collector output capacitance	$V_{CB}=10V$ , $f=1MHz$	—	—	50	pF

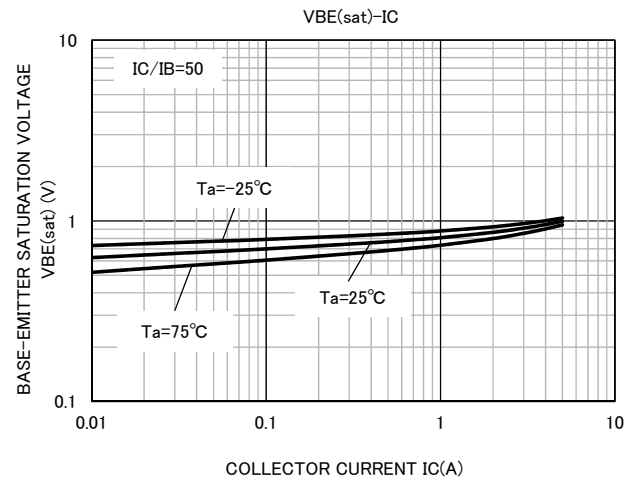
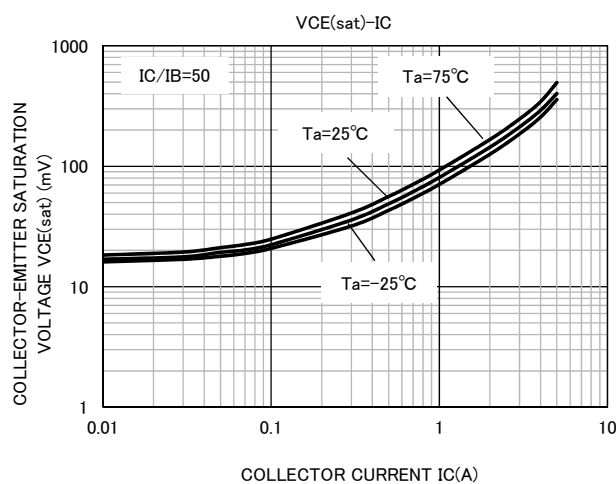
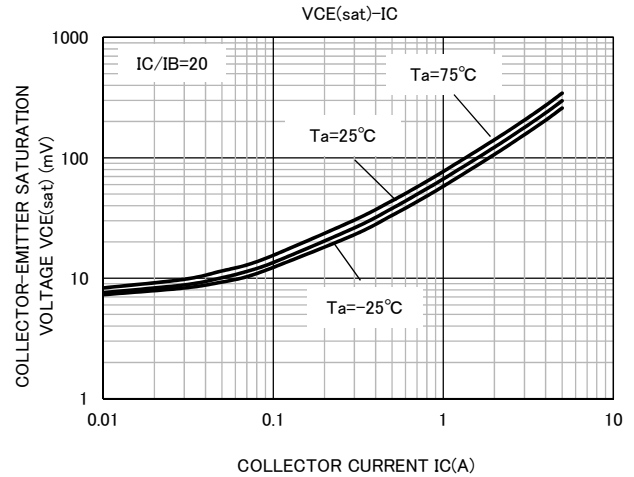
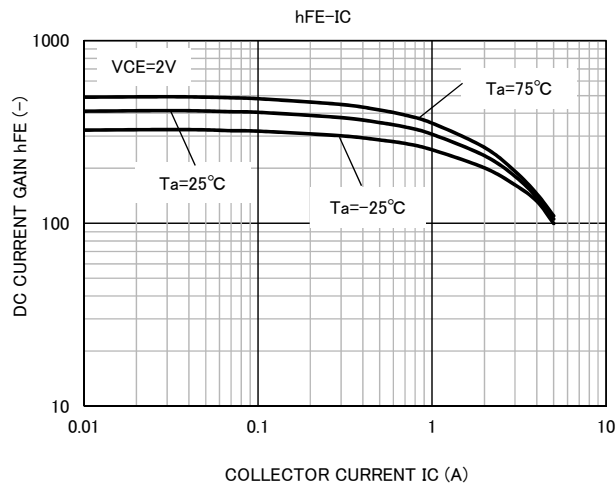
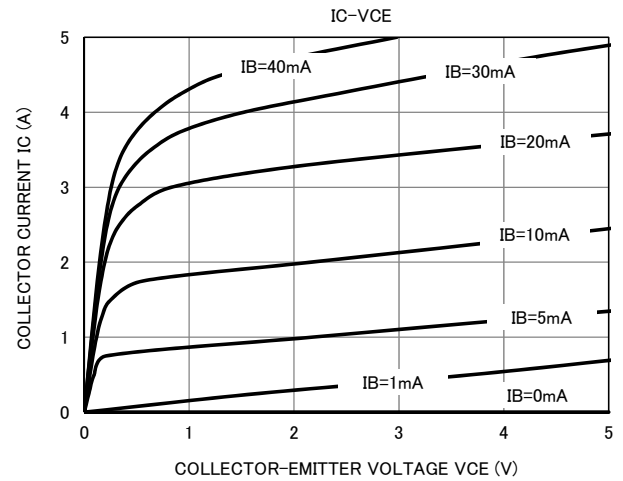
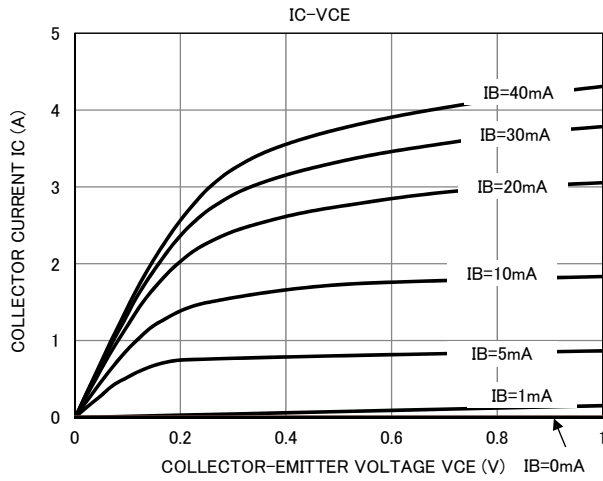
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## TYPICAL CHARACTERISTICS

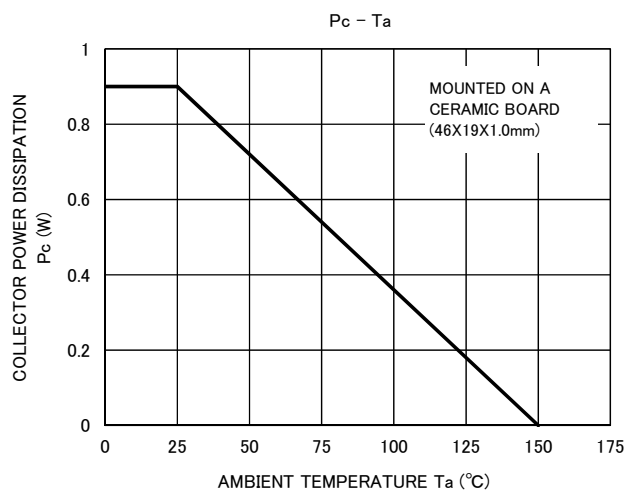
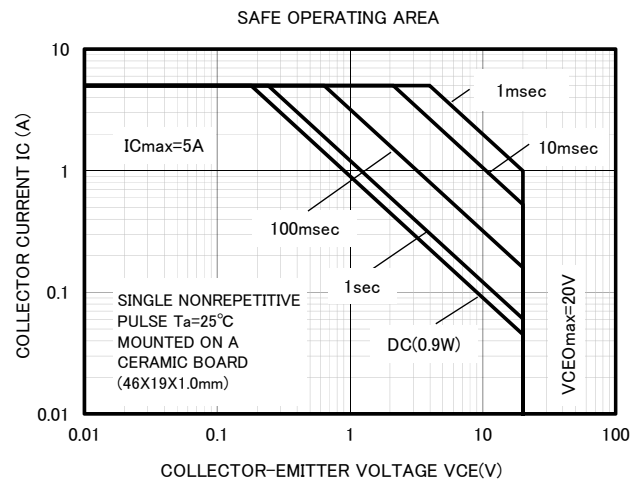
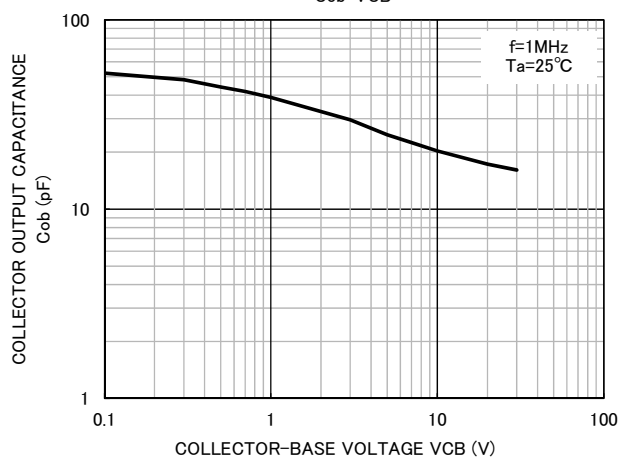
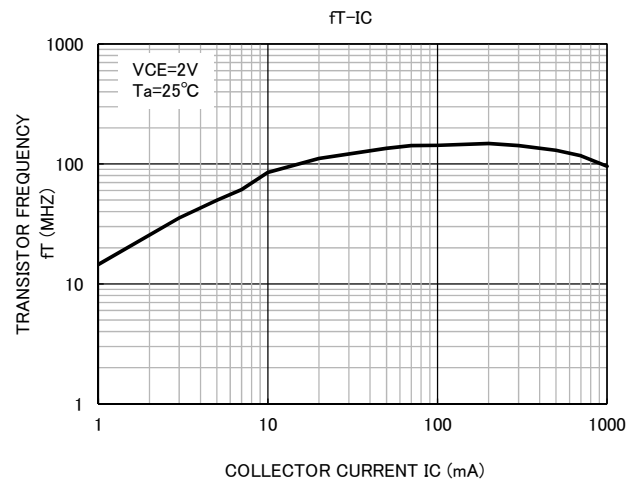
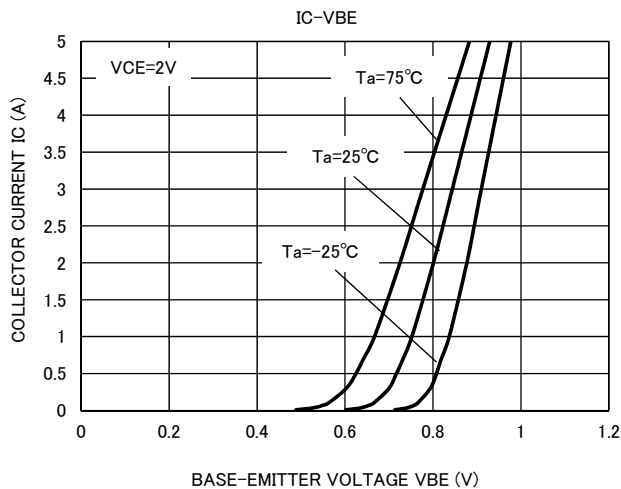


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